

Molding Type Module IGBT, 2 in 1 Package, 1200 V and 150 A



PRODUCT SUMMARY				
V_{CES}	1200 V			
I_C at T_C = 80 °C	150 A			
$V_{CE(on)}$ (typical) at $I_C = 150$ A, $T_J = 25$ °C	3.10 V			
Speed	8 kHz to 30 kHz			
Package	Double INT-A-PAK			
Circuit	Half bridge			

FEATURES

- 10 µs short circuit capability
- · Low switching losses
- · Rugged with ultrafast performance
- V_{CE(on)} with positive temperature coefficient
- Low inductance case
- Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- · Inductive heating
- Electronic welder
- · Switching mode power supplies

DESCRIPTION

Vishay's IGBT power module provides ultrafast switching speed as well as short circuit ruggedness. It is designed for applications such as electronic welder and inductive heating.

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Collector to emitter voltage	V _{CES}		1200		
Gate to emitter voltage	V _{GES}		± 20	V	
Collector current		T _C = 25 °C	280		
Collector current	Ic	T _C = 80 °C	150		
Pulsed collector current	I _{CM} ⁽¹⁾	t _p = 1 ms	300	Α	
Diode continuous forward current	I _F	T _C = 80 °C	150		
Diode maximum forward current	I _{FM} ⁽¹⁾	t _p = 1 ms	300		
Maximum power dissipation	P _D	T _J = 150 °C	1147	W	
Short circuit withstand time	T _{SC}	T _J = 125 °C	10	μs	
RMS isolation voltage	V _{ISOL}	f = 50 Hz, t = 1 min	2500	V	

Note

⁽¹⁾ Repetitive rating: Pulse width limited by maximum junction temperature.



IGBT ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V _{(BR)CES}	T _J = 25 °C	1200	-	-	
Collector to emitter saturation voltage	VCE(cot)	$V_{GE} = 15 \text{ V}, I_{C} = 150 \text{ A}, T_{J} = 25 ^{\circ}\text{C}$	-	3.10	3.60	v
Collector to enfitter saturation voltage		V _{GE} = 15 V, I _C = 150 A, T _J = 125 °C	-	3.45	-	V
Gate to emitter threshold voltage	V _{GE(th)}	$V_{CE} = V_{GE}$, $I_{C} = 1.5$ mA, $T_{J} = 25$ °C	4.4	5.2	6.0	
Collector cut-off current	I _{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0$ V, $T_{J} = 25$ °C	-	-	5.0	mA
Gate to emitter leakage current	I _{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0$ V, $T_{J} = 25$ °C	-	-	400	nA

SWITCHING CHARACTERISTICS						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Turn-on delay time	t _{d(on)}		-	612	-	ns mJ
Rise time	t _r		-	116	-	
Turn-off delay time	t _{d(off)}	V_{CC} = 600 V, I_C = 150 A, R_g = 6.8 Ω,	-	546	-	
Fall time	t _f	V _{GE} = ± 15 V, T _J = 25 °C	-	125	-	
Turn-on switching loss	E _{on}		-	17.7	-	
Turn-off switching loss	E _{off}		-	8.9	-	
Turn-on delay time	t _{d(on)}		-	609	-	ns ns
Rise time	t _r		-	116	-	
Turn-off delay time	t _{d(off)}	$V_{CC} = 600 \text{ V}, I_{C} = 150 \text{ A}, R_{g} = 6.8 \Omega,$	-	564	-	
Fall time	t _f	V _{GE} = ± 15 V, T _J = 125 °C	-	148	-	
Turn-on switching loss	E _{on}		-	17.5	-	I
Turn-off switching loss	E _{off}		-	11.0	-	- mJ
Input capacitance	C _{ies}		-	12.7	-	
Output capacitance	C _{oes}	$V_{GE} = 0 \text{ V}, V_{CE} = 30 \text{ V}, f = 1.0 \text{ MHz}$	-	1.14	-	nF
Reverse transfer capacitance	C _{res}		-	0.46	-	
SC data	I _{SC}	$\begin{array}{c} t_p \leq 10 \; \mu s, V_{GE} = 15 \; V, T_J = 25 \; ^{\circ}C, \\ V_{CC} = 600 \; V, V_{CEM} \leq 1200 \; V \end{array}$	-	1400	-	Α
Internal gate rsistance	R _g		-	2.4	-	Ω
Stray inductance	L _{CE}		=	-	18	nΗ
Module lead resistance, terminal to chip	R _{CC'+EE'}	T _C = 25 °C	=	0.32	-	mΩ

DIODE ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Forward voltage	V _F	I 100 A	T _J = 25 °C	-	1.75	2.15	V
Forward voltage		I _F = 100 A	T _J = 125 °C	-	1.80	-	
Reverse recovery charge	Q _{rr}	Q _{rr}	T _J = 25 °C	-	8.2	-	μC
neverse recovery charge			T _J = 125 °C	-	19.1	-	μΟ
Dools was a was a same a surrount		$I_{rr} = 150 \text{ A, } V_{R} = 600 \text{ V,}$ $dI_{F}/dt = -1500 \text{ A/}\mu\text{s}$ $V_{GE} = -15 \text{ V}$	T _J = 25 °C	-	85	-	_
Peak reverse recovery current	I _{rr}		T _J = 125 °C	-	125	-	A
D	г		T _J = 25 °C	-	4.2	-	I
Reverse recovery energy	E _{rec}		T _J = 125 °C	-	8.4	-	mJ



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction temperature range	TJ		-	-	150	°C
Storage temperature range	T _{Stg}		-40	-	125	°C
Junction to case	- R _{e,JC}		-	-	0.109	
Diode	L _θ JC		-	-	0.180	K/W
Case to sink (Conductive grease applied)	R _{θCS}		-	0.035	-	
Mounting torque		Power terminal screw: M5		2.5 to 5.0		Nm
		Mounting screw: M6	3.0 to 6.0		INIII	
Weight		Weight of module	-	300	-	g

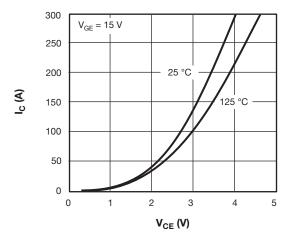


Fig. 1 - IGBT Typical Output Characteristics

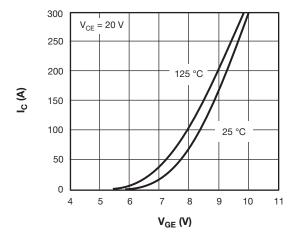


Fig. 2 - IGBT Typical Transfer Characteristics

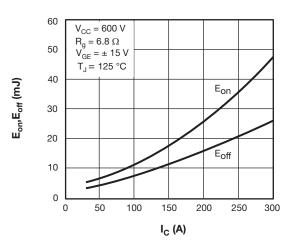


Fig. 3 - IGBT Switching Loss vs. I_C

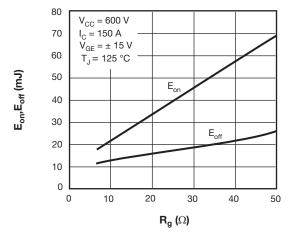
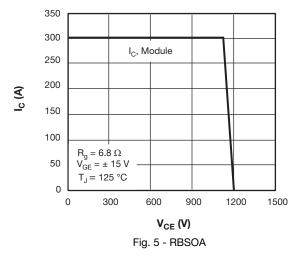


Fig. 4 - IGBT Switching Loss vs. R_g



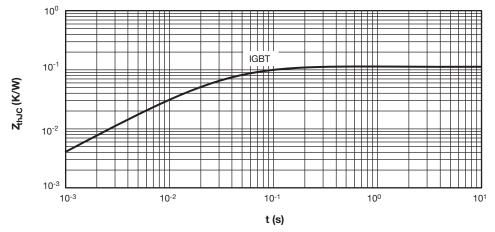


Fig. 6 - IGBT Transient Thermal Impedance

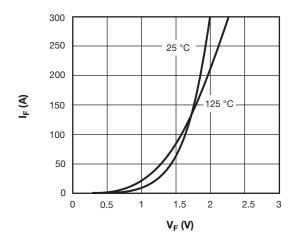


Fig. 7 - Diode Typical Forward Characteristics

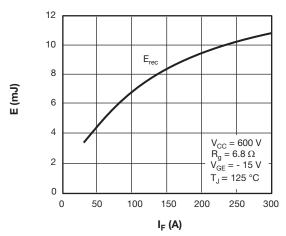


Fig. 8 - Diode Switching Loss vs. I_F

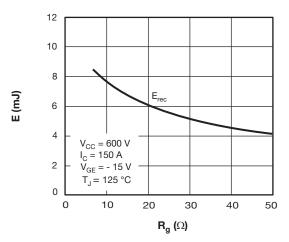


Fig. 9 - Diode Switching Loss vs. Rq

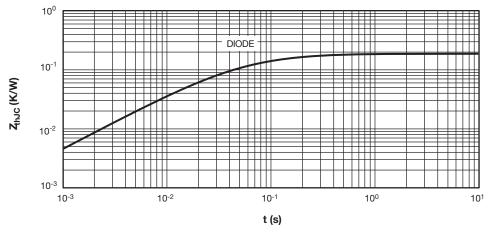
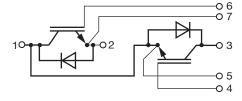


Fig. 10 - Diode Transient Thermal Impedance

CIRCUIT CONFIGURATION

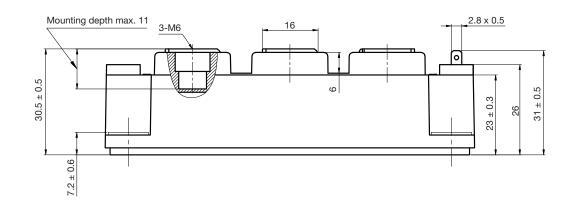


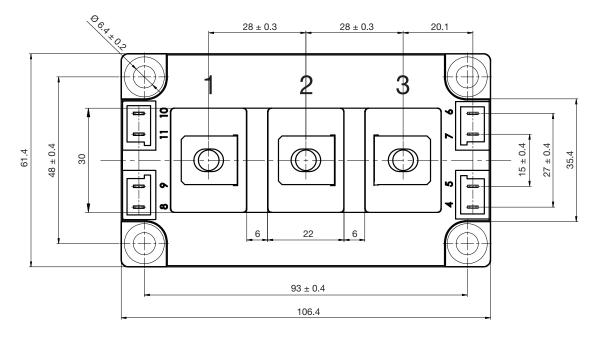
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95525			



Double INT-A-PAK

DIMENSIONS in millimeters (inches)







Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000